

Claims

[c1] What is claimed is:

1.A method for manufacturing a light emitting diode having a transparent substrate, the method comprising:
forming a semiconductor multilayer on a first substrate producing a first multilayer structure;
forming an amorphous interface layer on a second substrate, the second substrate being transparent in nature, producing a second multilayer structure;
bonding the first multilayer structure to the second multilayer structure, producing a third multilayer structure;
and
removing the first substrate from the third multilayer structure.

[c2] 2.The method of claim 1 further comprising a step of forming a transparent conductive layer on the third multilayer structure after removing the first substrate.

[c3] 3.The method of claim 1, wherein the amorphous interface layer is made of at least one selected from a group comprising indium tin oxide, indium cadmium oxide, indium tin oxide, and transparent conductive adhesive agent.

- [c4] 4.A method for manufacturing a light emitting diode, comprising:
forming a semiconductor multilayer on a first substrate
producing a first multilayer structure;
forming an amorphous interface layer on a second substrate, the second substrate being transparent in nature,
producing a second multilayer structure;
bonding the first multilayer structure to the second multilayer structure, producing a third multilayer structure;
and
removing the first substrate from the third multilayer structure.
- [c5] 5.The method of claim 4 further comprising a step of forming a transparent conductive layer on the third multilayer structure after removing the first substrate.
- [c6] 6.The method of claim 4, wherein the amorphous interface layer is made of at least one selected from a group comprising indium tin oxide, cadmium tin oxide, antimony tin oxide, and transparent conductive adhesive agent.